Form 1449*	Atty. Docket No.: 303.678US4	Serial No. ~~Unknown~~ 09/943,393
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
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U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
PD	5,668,035	09/16/1997	Fang, C.H., et al.	438	239	06/10/96
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FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes / No

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*Substitute Disclosure Statement Form (PTO-1449)

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Sheet 2 of 2

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